

Automotive IC Packaging: Evolving Power Solutions

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What We Will Cover:

- Automotive Market Trends & Evolution Market Growth & Key Package Enablers
- Automotive Package Options/Roadmap
- Next Generation Power Enablers:
 Direct Cu-to-Cu Interconnect



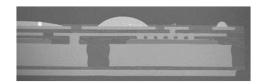






Automotive Market Trends & Evolution

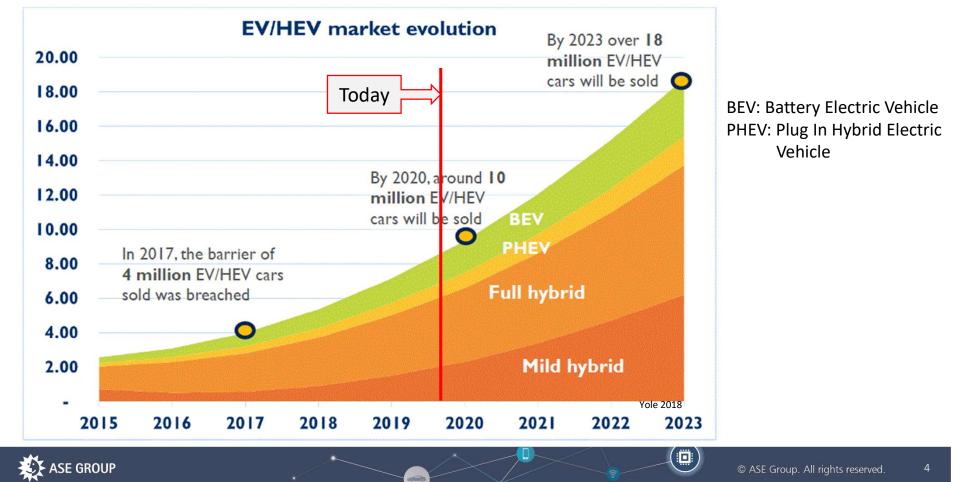
Market Growth and Key Focus







EV/HEV Market Forecast



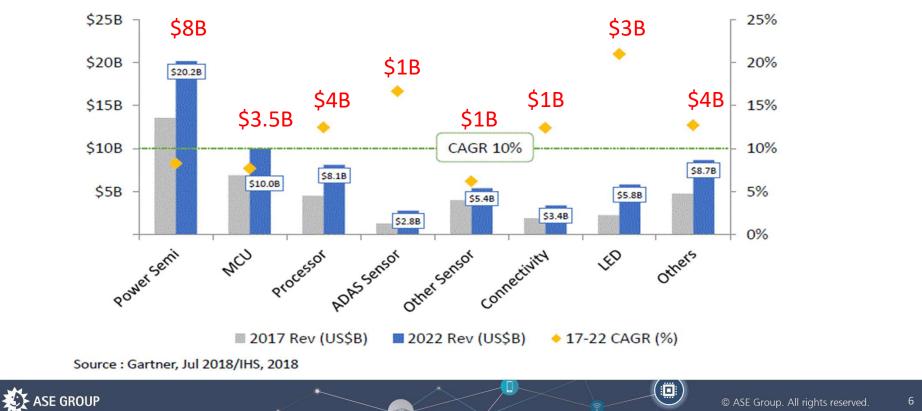
EV/HEV Power Modules Market Data

- Each EV/HEV Car Requires 5 Power modules
 - 50kW to 300kW: Inverters
 - 10kW to 40kW: Starter- Generators
 - 4kW to 20kW: Battery Chargers
 - 2kW-8kW: Battery DC-DC Converters
 - 500W 3kW: Power Steering, Water Pump, Climate Compressor
- EV/HEV accounts for half the WW power module market value in 2017, and 80% of the produced power module units
- EV/HEV only accounts for 4% of new cars in 2018
- Forecasts ranges for EV/HEV in 2030 is between 40% and 80% of all new annual vehicle sales
- EV/HEV cars will grow from 4Mu in 2018 to between 50Mu and 100Mu in 2030 (10x-20x Growth)



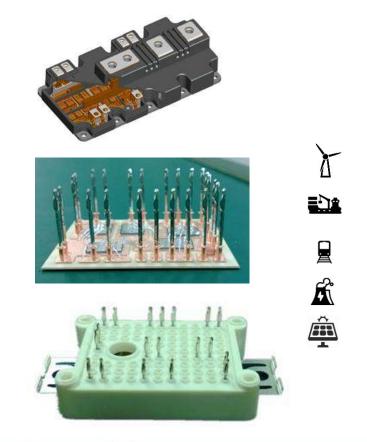


Automotive Semiconductor Content By Device



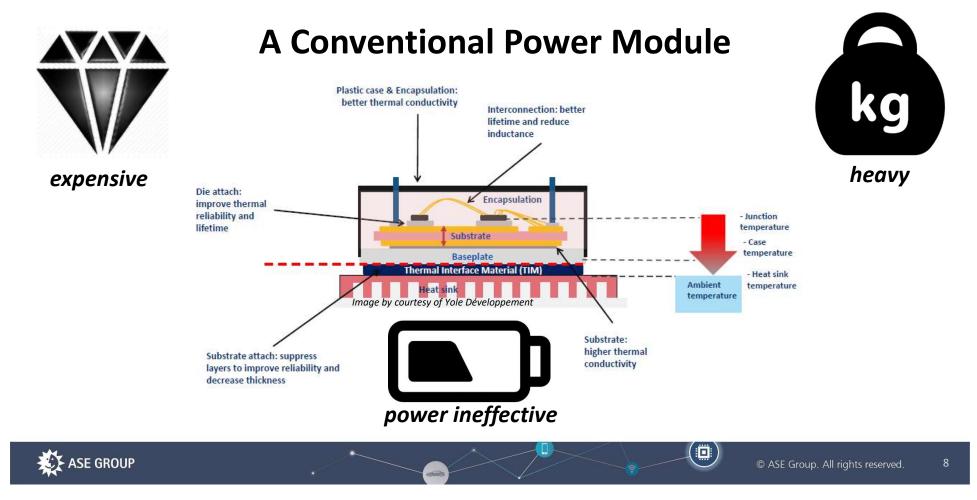
Conventional/Traditional Type of High Power Modules

- Singulated Processing
- Large All-In-One Modules
- Specific Expensive BOM (DBC Ceramic Subm,, GEL Filling, Plastic Housing, Large Silicon Dies
- SnPb Die Attach (With Lead)
- Vacuum Soldering
- Bottom Side Cooling Only
- Complex structure with cleanable baseplate for over 30yr useage
- Ok for trains, Windmills, Power, Power Stations, Solar Panels
- Not Suitable for high volumes (x10's from today)





A 30-year Old Technology Designed For The Conservative Industrial World



Technology Trend for Power Electronics in EV/HEV

Objective \$/kW Lower cost kW/kg Higher power density



Smaller size

System Level

- More integration like motor + inverter
- High Temperature Capacitors, Laminated ٠ busbars
- Enhanced cooling of the power converter, ٠ Double-sided cooling

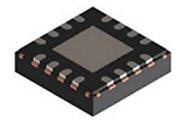
Module/Packaging Level

- Double-sided cooling
- Use epoxy resin as encapsulant
- Silver Sintering is promising die attach ٠ material for power packaging

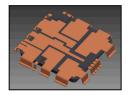
Device Level

Wide band gap material will emerge (SiC, • GaN) as new material for power semiconductor

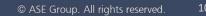




Power Package Options (Automotive)





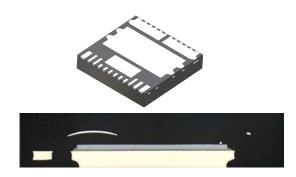


Power & Module QFN

- Power QFN development
 - High Thermal requirement
 - 20 mil thick LF: Under mass production

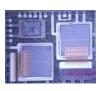
Integrated L/F power module development

- 6-MOSFET + 1 shunt resistor
- High Pb solder D/A
- Al wedge bonding (3mil Gate / 20mil source)
- Module QFN
 - Component integrated
 - HV / LV MOSFET + control chip
 - Half-bridge application as 2 HV MOSFET + 2 LV MOSFET + 2 control chips

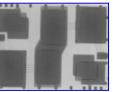






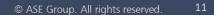


Half Bridge Power QFN

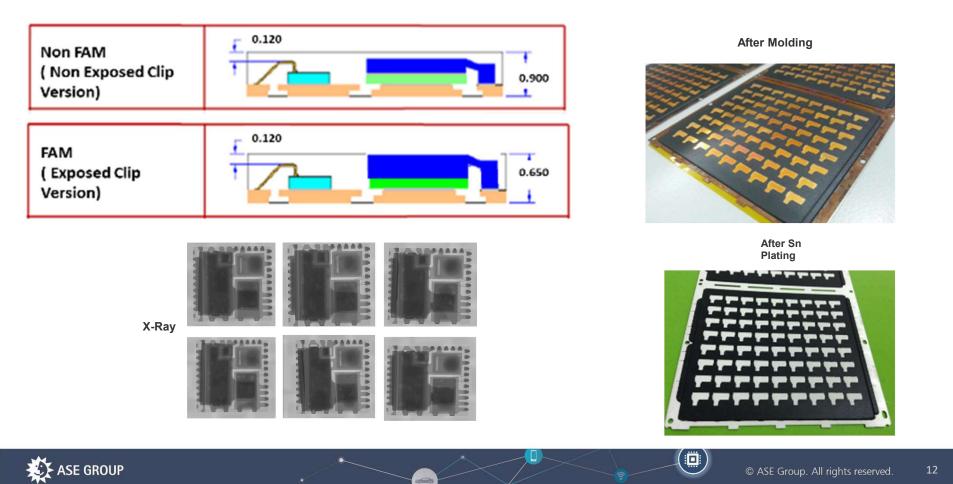


Full Bridge Power QFN With wettable flank





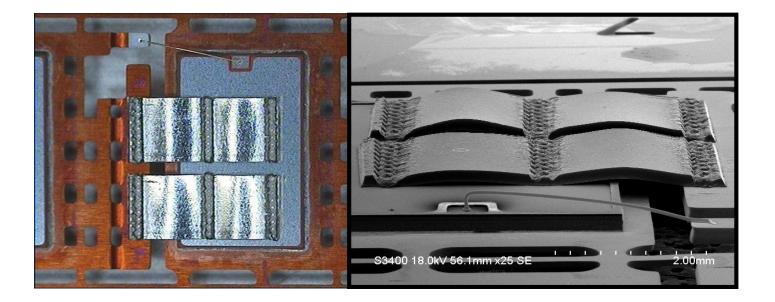
PQFN with Cu clip – Package Structure



Wettable 7x8PQFN with Al Ribbon - AEC Q101

Package structure & BOM

DFN 11L 8X7 BODY DIE SIZE : 235X143MIL



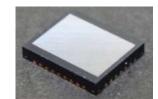


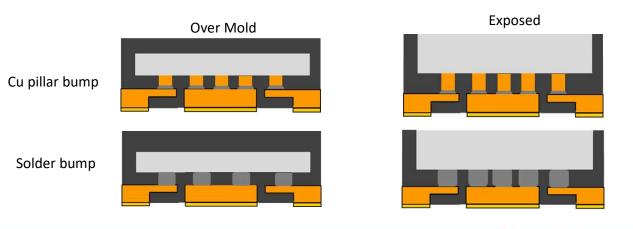


Flip Chip QFN (FCQFN)

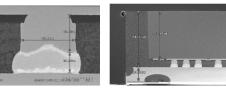
FCQFN Structure & Benefit

- Low Rds-on for power management device by reducing wire trace to have lower power consumption
- High Current solution for Power device/ Low IR Drop
- High Thermal solution
- Short process flow & CT
- W/ & W/O die exposed solution
- Low cost compared with FC CSP

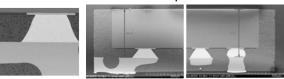




Cu pillar bump



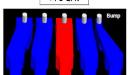
Solder bump

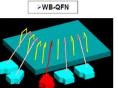


IR Drop Evaluation for WB-QFN and

FC-QFN

>FC-QFN





 Resistance simulation by ANSYS 03D

 PKG Type
 PKG Size (mm²)
 Resistance (mOhm)

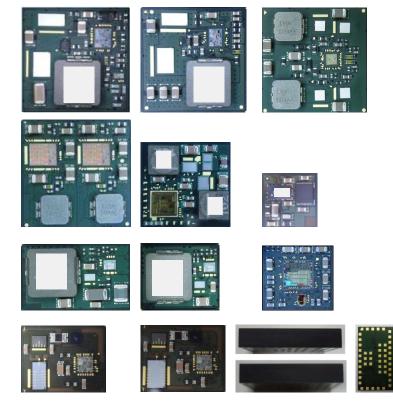
 FC-QFN
 5 X 5
 6
 5

 WB-QFN
 5 X 5
 65
 55

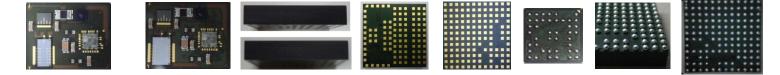
According to the resistance evaluation, it has about 90% resistance reduction from WB-QFN design to FC-QFN design. Thus, there is about 90% IR-drop improvement.



uPower Module



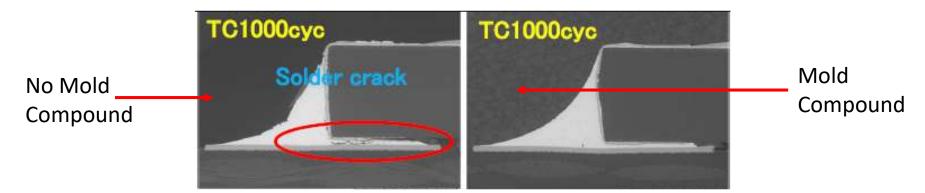
- Application: DC-DC Converter / Smart Voltage regulator
- Requirements:
 - Solder D/A and epoxy D/A
 - R/L/C & Inductor (or diode, transformer) handling (Max.7x7.6x2mm)
 - Flip-chip, Multi die and multi wire handling
 - High Reliability for automotive application
 - Thick mold cavity (Max. 4mm)
- Status:
 - Started Vol. Production from Dec '13
 - Automotive uPower Module production from Oct'14





Benefits of Molding: Molded SiP vs PBA (System on Board)

- Improved thermal cycling compliance
- Higher immunity to vibrations



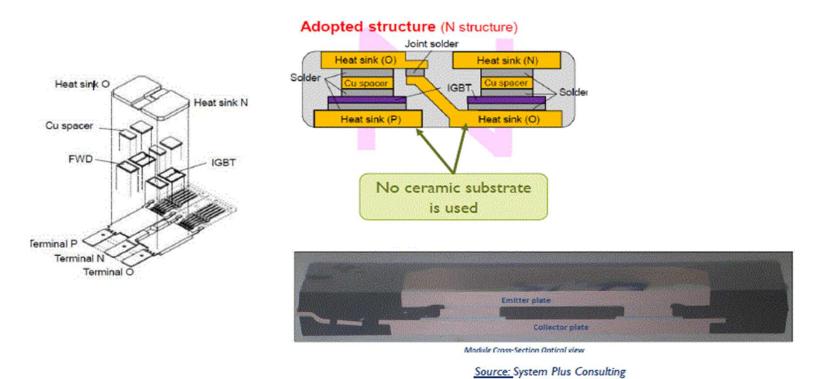
Good protection ECU with direct molding, while solder crack occurs at solder joint of the chip resistance without mold

By courtesy of Sumitomo Bakelite



Other Industry Solutions – Improved Thermal

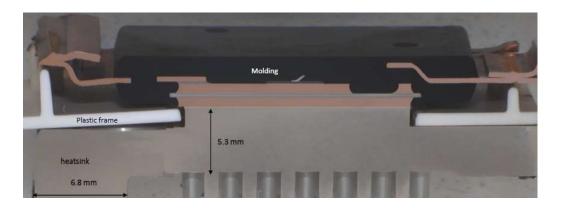
Toyota Prius Fourth Generation – Double Sided Cooling Power Card





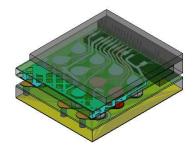
Other Industry Solutions – Improved Thermal/Electrical

- Custom Leadframe Tooling
- Batch Processing (strips, panels)
- Modularized (multiple packages in module)
- Semiconductor -like BOM & structure (leadframe, embedding, overmolding)
- Smaller SiC and GaN dies
- Lead-free die attach (TLPB, Ag sintering)
- Reflow with (limited) pressure

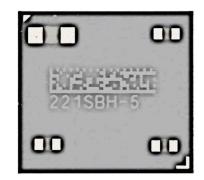








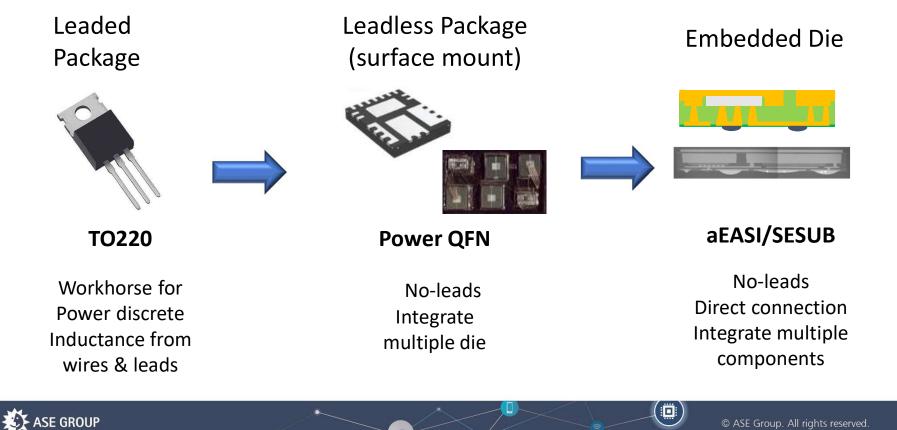
Next Generation Power Enablers: Direct Cu-to-Cu Interconnect



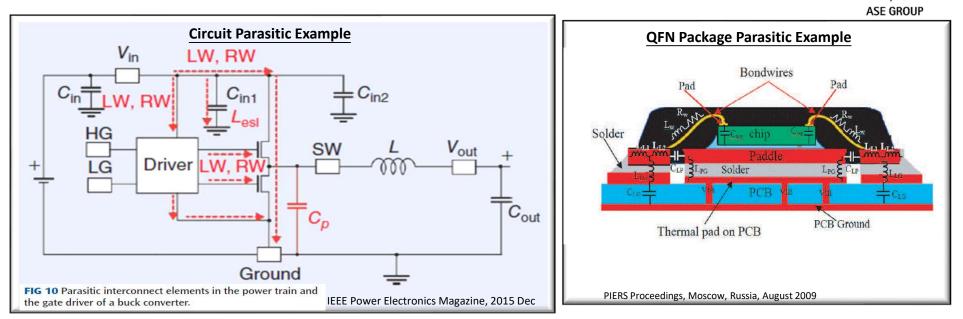


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Power Discrete & SiP – How packaging is evolving.....



Electrical Considerations of Embedding

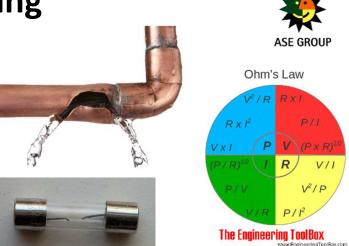


ligh Capacitance Can Create Parasitic Crosstalk and Inductance Drives Power Loss

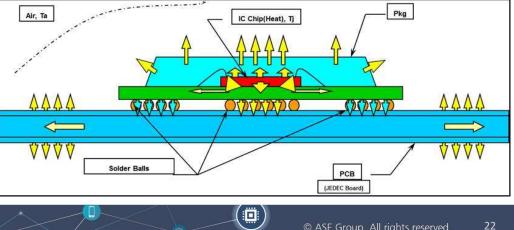


Understanding Ohms Law for Packaging

- Ohm's Law : Power Loss = Current Squared x Resistance 0 (Double the Current give you 4x the Power Loss)
- Physical Explanation The voltage difference along a wire 0 depends on the current – More current flowing with resistance mean more voltage (pressure of electricity if you like) is built up.
- Practical Explanation Power measured 0 in watts is equal to I² x R along the path of circuit. If you keep resistance small, you minimize power loss as HEAT!!



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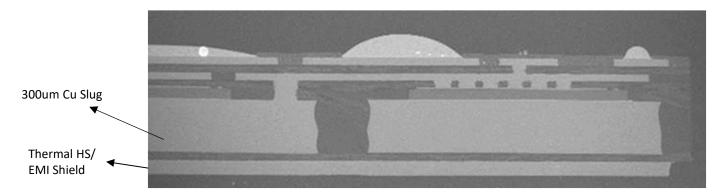


**Physics Forum 2008



What's a-EASI? aEASI = Advanced Embedded Active System Integration

- Utilizes Mature Organic Substrate Process Modified to Meet High Power Applications
- Hybrid Power Package Combining Lead frame & Substrate Technologies
- Good Current Capability- ~60A (Integrated Power Stage Example), ~ 1.9W/mm2
- 300um thick Copper Heat Spreader/Electrical Pad (Back of Die)
- Deep Full Filled Vias to Die ~ 130um Diam
- Ultra Low Resistivity Die Attach Interface



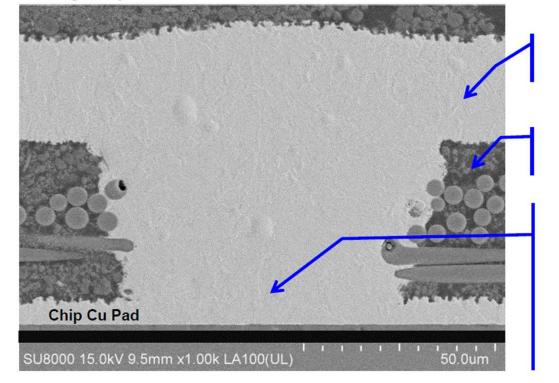
P1 Example





aEASI P1 Package to Die Interconnect Highlights

* Design for power devices

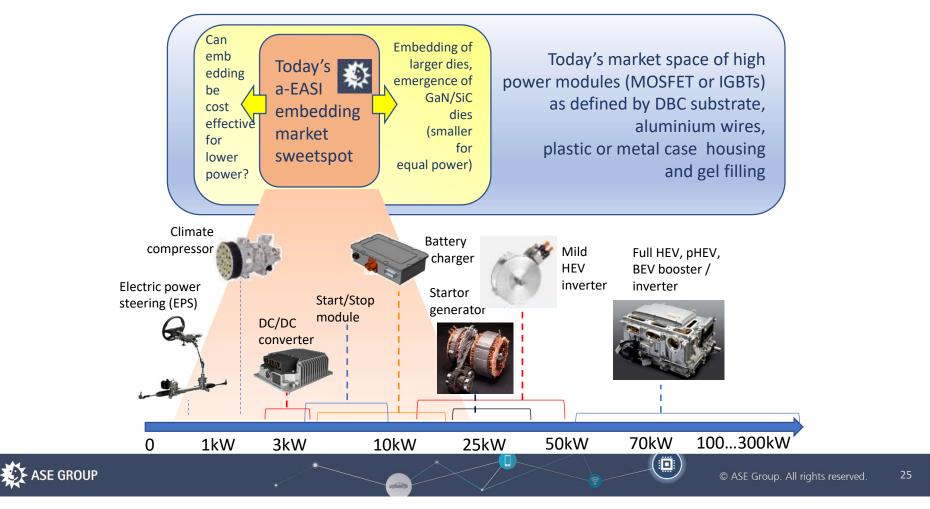


- Thick Cu RDL (32 um). Minimize turn on resistance.
- Prepreg material provide >2.5KV breakdown voltage
- 50um via diameter (Equal to 4 x 1 mil wire bond in conductor area)
- Cu to Cu interface.
 Minimize reliability risk in high current density condition

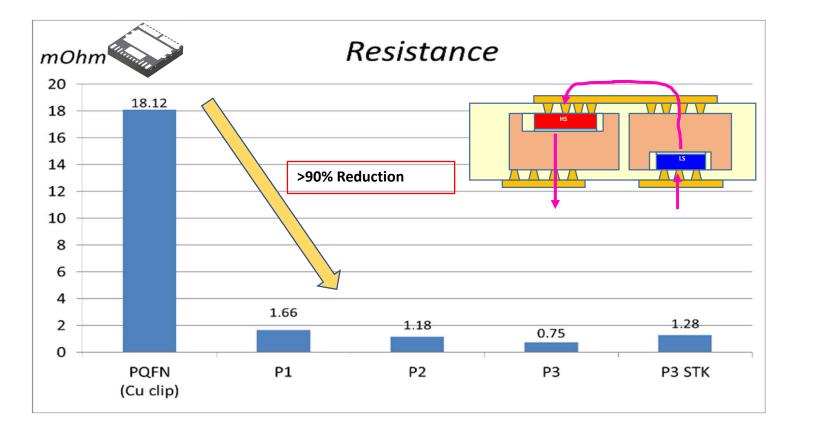




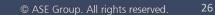
a-EASI Embedded Market Application in Electrified Cars



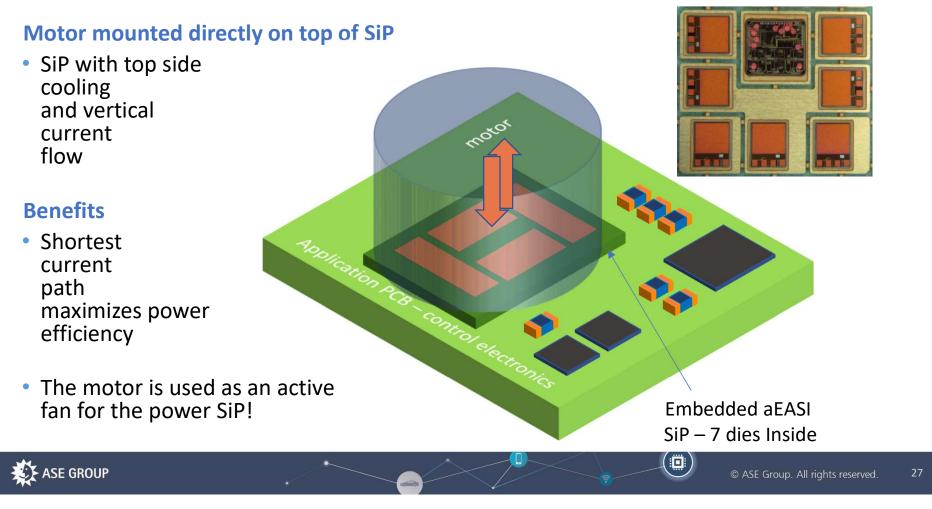
aEASI Electrical Performance Comparison







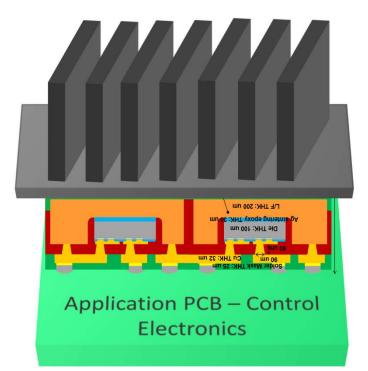
High Efficiency Electric Motor Pump in EV/HEV cars



Application to DC/DC Converter for Automotive

Embedded aEASI SiP:

- Reduce Parasitic Inductance
- Enable higher frequency of operation (250kHz instead of 80KHz)
- Enable Big Reduction in Passives (L & C) in buck/boost circuit
- Reduce total size & cost of the converter module





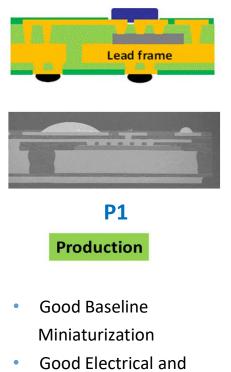
Thank You

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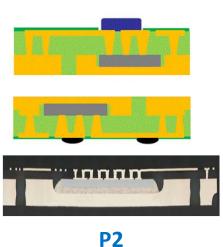




aEASI Package Portfolio



 Good Electrical and Thermal



Production

- Superior Thermal w/ Cavity Exposed Pad
- Thinner Solution
- Double Sided Thermal Capability







P3 Qualified

- Multiple Vertical Current Flow Die Stack
- Higher Level of Integration Options

